NSN 5961-01-281-5027

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-281-5027 **Inclosure Material:** Metal **Overall Length:** 1.222 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-4 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Criticality Code Justification:** Zzzy **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 20.00 amperes forward current, average absolute **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Item must comply with requirements of defense supply center columbus production standard no. Lo4005 **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Reference Number Differentiating Characteristics:** Areference number differentiating material will be in accordance with naval inventory control point activity hx quality control. Manufacturing and testing specifications available at the dla icp Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

No